

In the Specification

At page 1, before the "Technical Field" section, please insert:

RELATED PATENT DATA

This patent resulted from a continuation application of U.S. Patent Application Serial No. 09/943,186, which was filed August 29, 2001.

Please amend paragraph 0032 as follows:

[0032] Fig. 3 illustrates semiconductor material wafer 24 at a processing step encompassed by a method of the present invention. Reticle 10 is shown over wafer 24, and is shown to comprise the rectangular shape shown in Fig. 1. It is to be understood, however, that the invention can comprise reticles having shapes other than the shown rectangular shape. Reticle 10 would typically be elevated above wafer 24, and held in position relative to wafer 24 by a photolithographic processing apparatus (not shown) to form the assembly 18 described with reference to Fig. 2 & 3. Further, reticle 10 would comprise a pattern of openings formed therein, such as, for example, the openings 16 shown in Fig. 1. Such openings are not illustrated in Fig. 3 in order to simplify the illustration and the discussion that follows.

Please amend paragraph 0044 as follows:

[0044] In the particular embodiment in which portions 50 were formed to be spaced by a minimum feature spacing of a photolithographic process, it is noted that exposed portions 70 will actually correspond to features identical to those defined by exposed portions 50, and formed between the exposed portions 50. Accordingly, exposed portions 70 define features which are separated from those of exposed portions 50 by less than the minimum feature spacing associated with the photolithographic process. Although the shown embodiment illustrates features 70 as being ~~discreet~~ discrete from features 50, it is to be understood that methodology of the present invention can be utilized to form features with a second exposure pattern which are joined with features formed by a first exposure pattern.